

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of:	)	
	)	Examiner: Bradley K. Smith
<b>Chau, et al.</b>	)	
	)	Art Unit: 2891
Application No: 10/760,028	)	
	)	Atty Docket No.: 42P17814
Filed: January 16, 2004	)	
	)	Confirmation No.: 8503
For: TRI-GATE TRANSISTORS AND	)	
METHODS TO FABRICATE SAME	)	
	)	

**Mail Stop Issue Fee**

Assistant Commissioner For Patents

P.O. Box 1450

Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT AFTER ALLOWANCE**

In accordance with Applicant's duty of disclosure, this Information Disclosure Statement, substitute for form 1449A/PTO (based on PTO/SB/08A), and cited reference(s) are being submitted after allowance of this application but prior to payment of the Issue Fee. It is respectfully requested that the cited reference(s) be placed in the file and that the subject application not be withdrawn from issue.

The fee set in the amount of \$180.00 for submission of the Information Disclosure Statement is enclosed herewith.

The submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made in the subject application and is not to be construed as an admission that the information cited in this statement is material to patentability.

**Filed via EFS Web – July 5, 2007**

The Commissioner is authorized to charge any deficiencies or credit any overpayments in connection with this submission to Deposit Account No. 02-2666, and is requested to notify us of same.

Respectfully submitted,  
**BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN, LLP**

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Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(Use as many sheets as necessary)</i>	Complete if Known	
	<b>Application Number</b>	10/760,028
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	<b>First Named Inventor</b>	Jin, Been-Yih
	<b>Group Art Unit</b>	2891
	<b>Examiner Name</b>	Smith, Bradley
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
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